

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional)

FIS9-2000-0372-US1

Application Number

09/878,556

Applicant(s)

S. Sundar Kumar Iyer et al.

Filing Date

6/11/01

Group Art Unit

2813

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
~	AA	3,549,368	12/22/1970	R. H. Collins et al.	—	—	—
~	AB	4,471,373	9/11/1984	Shimizu et al.	—	—	—
~	AC	4,651,406	3/24/1987	Shimizu et al.	—	—	—
~	AD	5,965,005	10/12/1999	Lee et al.	—	—	—

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
~	AE	JP4025130	1/28/1992	Japan	—	—		✓
~	AF	WO 98/08252	2/26/1998	Europe	—	—		✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

~	AG	"Porous Silicon: The material and its applications to SOI technologies" by G. Bomchil, A. Halimaoui, and R. Herino from Microelectronic Engineering 8 (1988) pp. 293-310, Elsevier Science Publishers B.V. (North-Holland).
~	AH	"Electrical Characterization of SOI Materials and Devices", by Sorin Cristoloveanu and Sheng S. Li, (1st ed., 1995) pp. 28-31, Kulwer Academic Press.

EXAMINER

Harfor Sank Chen

DATE CONSIDERED

8/11/02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.